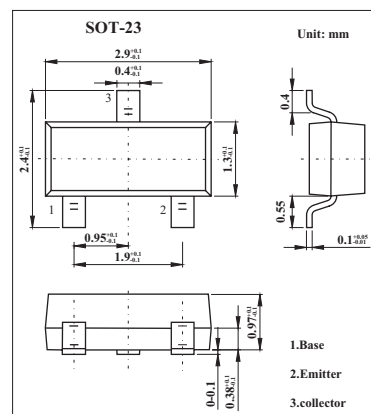


General Purpose Transistor

2SD2226K

■ Features

- High DC current gain.
- High emitter-base voltage.
- Low saturation voltage.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	60	V
Collector-emitter voltage	V_{CE0}	50	V
Emitter-base voltage	V_{EB0}	12	V
Collector current	I_c	0.15	A
		0.2 *	
Collector power dissipation	P_c	0.2	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* Single pulse $P_w=100\text{ms}$.

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CB0}	$I_c=10\mu\text{A}$	60			V
Collector-emitter breakdown voltage	BV_{CE0}	$I_c=1\text{mA}$	50			V
Emitter-base breakdown voltage	BV_{EB0}	$I_E=10\mu\text{A}$	12			V
Collector cutoff current	I_{CB0}	$V_{CB}=50\text{V}$			0.3	μA
Emitter cutoff current	I_{EB0}	$V_{EB}=12\text{V}$			0.3	μA
Collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_c/I_E=50\text{mA}/5\text{mA}$			0.3	V
DC current transfer ratio *	h_{FE}	$V_{CE}=5\text{V}, I_c=1\text{mA}$	820		2700	
Output capacitance *	f_T	$V_{CE}=5\text{V}, I_E=-10\text{mA}, f=100\text{MHz}$		250		MHz
Transition frequency	C_{ob}	$V_{CB}=5\text{V}, I_E=0, f=1\text{MHz}$		3.5		pF

* Measured using pulse current.

■ h_{FE} Classification

Marking	BJ	
Rank	V	W
h_{FE}	820~1800	1200~2700